

P6SMB6.8AT3 Series, SZP6SMB6.8AT3 Series

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ $T_L = 25^\circ\text{C}$, Pulse Width = 1 ms	P_{PK}	600	W
DC Power Dissipation @ $T_L = 75^\circ\text{C}$ Measured Zero Lead Length (Note 2) Derate Above 75°C	P_D	3.0 40	W mW/ $^\circ\text{C}$
Thermal Resistance from Junction-to-Lead	$R_{\theta JL}$	25	$^\circ\text{C/W}$
DC Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	0.55 4.4	W mW/ $^\circ\text{C}$
Thermal Resistance from Junction-to-Ambient	$R_{\theta JA}$	226	$^\circ\text{C/W}$
Forward Surge Current (Note 4) @ $T_A = 25^\circ\text{C}$	I_{FSM}	100	A
Operating and Storage Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 10 X 1000 μs , non-repetitive
- 1" square copper pad, FR-4 board
- FR-4 board, using ON Semiconductor minimum recommended footprint, as shown in 403A case outline dimensions spec.
- 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

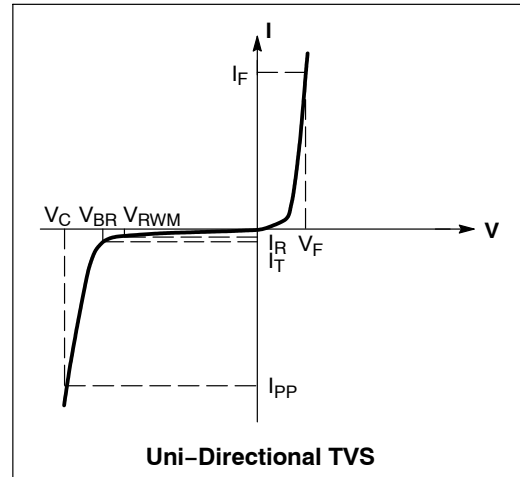
ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 3.5\text{ V Max. @}$

I_F (Note 4) = 30 A) (Note 5)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
ΘV_{BR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F

- 1/2 sine wave or equivalent, PW = 8.3 ms, non-repetitive duty cycle



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ELECTRICAL CHARACTERISTICS (Devices listed in bold, italic are ON Semiconductor Preferred devices.)

Device*	Device Marking	V _{RWM} (Note 6)	I _R @ V _{RWM}	Breakdown Voltage				V _C @ I _{PP} (Note 8)		θV _{BR}	C _{typ} (Note 9)
				V _{BR} V (Note 7)			@ I _T	V _C	I _{PP}		
		V	μA	Min	Nom	Max	mA	V	A	%/°C	pF
SZ/P6SMB6.8AT3, G	6V8A	5.8	1000	6.45	6.8	7.14	10	10.5	57	0.057	2380
P6SMB7.5AT3, G	7V5A	6.4	500	7.13	7.51	7.88	10	11.3	53	0.061	2180
P6SMB8.2AT3, G	8V2A	7.02	200	7.79	8.2	8.61	10	12.1	50	0.065	2015
P6SMB9.1AT3, G	9V1A	7.78	50	8.65	9.1	9.55	1	13.4	45	0.068	1835
P6SMB10AT3, G	10A	8.55	10	9.5	10	10.5	1	14.5	41	0.073	1690
P6SMB11AT3, G	11A	9.4	5	10.5	11.05	11.6	1	15.6	38	0.075	1550
P6SMB12AT3, G	12A	10.2	5	11.4	12	12.6	1	16.7	36	0.078	1435
P6SMB13AT3, G	13A	11.1	5	12.4	13.05	13.7	1	18.2	33	0.081	1335
SZ/P6SMB15AT3, G	15A	12.8	5	14.3	15.05	15.8	1	21.2	28	0.084	1175
SZ/P6SMB16AT3, G	16A	13.6	5	15.2	16	16.8	1	22.5	27	0.086	1110
SZ/P6SMB18AT3, G	18A	15.3	5	17.1	18	18.9	1	25.2	24	0.088	1000
SZ/P6SMB20AT3, G	20A	17.1	5	19	20	21	1	27.7	22	0.09	910
P6SMB22AT3,G	22A	18.8	5	20.9	22	23.1	1	30.6	20	0.092	835
P6SMB24AT3, G	24A	20.5	5	22.8	24	25.2	1	33.2	18	0.094	775
SZ/P6SMB27AT3, G	27A	23.1	5	25.7	27.05	28.4	1	37.5	16	0.096	700
SZ/P6SMB30AT3, G	30A	25.6	5	28.5	30	31.5	1	41.4	14.4	0.097	635
SZ/P6SMB33AT3, G	33A	28.2	5	31.4	33.05	34.7	1	45.7	13.2	0.098	585
SZ/P6SMB36AT3, G	36A	30.8	5	34.2	36	37.8	1	49.9	12	0.099	540
SZ/P6SMB39AT3, G	39A	33.3	5	37.1	39.05	41	1	53.9	11.2	0.1	500
P6SMB43AT3, G	43A	36.8	5	40.9	43.05	45.2	1	59.3	10.1	0.101	460
SZ/P6SMB47AT3, G	47A	40.2	5	44.7	47.05	49.4	1	64.8	9.3	0.101	425
SZ/P6SMB51AT3, G	51A	43.6	5	48.5	51.05	53.6	1	70.1	8.6	0.102	395
SZ/P6SMB56AT3, G	56A	47.8	5	53.2	56	58.8	1	77	7.8	0.103	365
SZ/P6SMB62AT3, G	62A	53	5	58.9	62	65.1	1	85	7.1	0.104	335
P6SMB68AT3, G	68A	58.1	5	64.6	68	71.4	1	92	6.5	0.104	305
P6SMB75AT3, G	75A	64.1	5	71.3	75.05	78.8	1	103	5.8	0.105	280
P6SMB82AT3, G	82A	70.1	5	77.9	82	86.1	1	113	5.3	0.105	260
P6SMB91AT3, G	91A	77.8	5	86.5	91	95.5	1	125	4.8	0.106	235
P6SMB100AT3, G	100A	85.5	5	95	100	105	1	137	4.4	0.106	215
P6SMB110AT3, G	110A	94	5	105	110.5	116	1	152	4.0	0.107	200
P6SMB120AT3, G	120A	102	5	114	120	126	1	165	3.6	0.107	185
P6SMB130AT3, G	130A	111	5	124	130.5	137	1	179	3.3	0.107	170
SZ/P6SMB150AT3, G	150A	128	5	143	150.5	158	1	207	2.9	0.108	150
SZ/P6SMB160AT3, G	160A	136	5	152	160	168	1	219	2.7	0.108	140
SZ/P6SMB180AT3, G	180A	154	5	171	180	189	1	246	2.4	0.108	130
SZ/P6SMB200AT3, G	200A	171	5	190	200	210	1	274	2.2	0.108	115

6. A transient suppressor is normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal to or greater than the DC or continuous peak operating voltage level.

7. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.

8. Surge current waveform per Figure 2 and derate per Figure 3.

9. Bias Voltage = 0 V, F = 1 MHz, T_J = 25°C

*The "G" suffix indicates Pb-Free package available.

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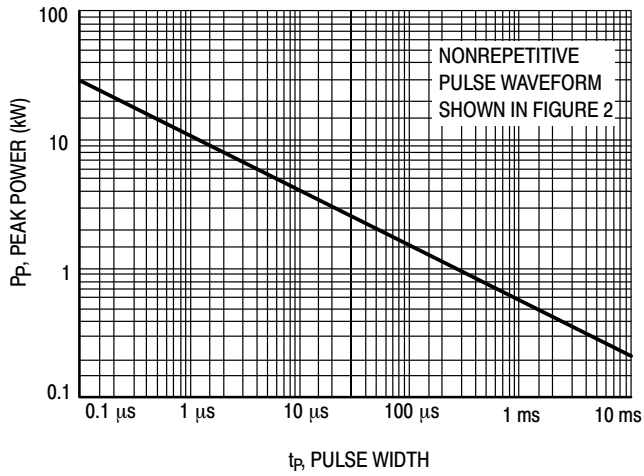


Figure 1. Pulse Rating Curve

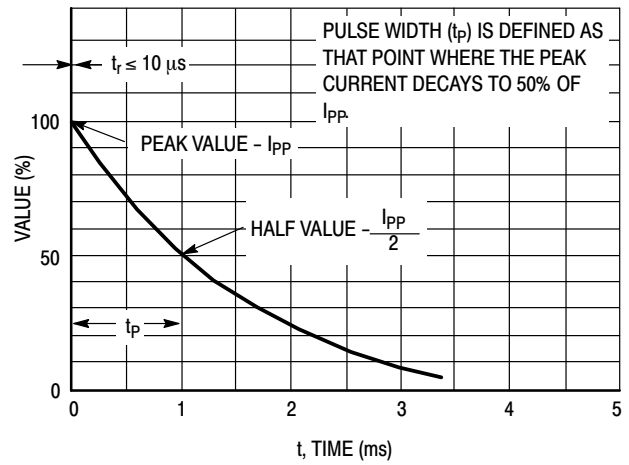


Figure 2. Pulse Waveform

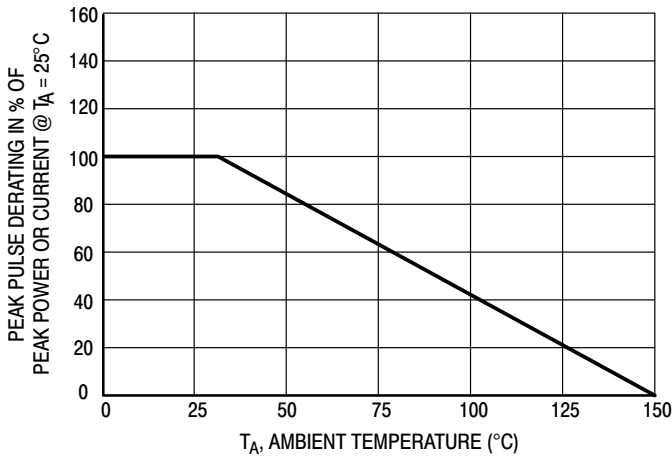


Figure 3. Pulse Derating Curve

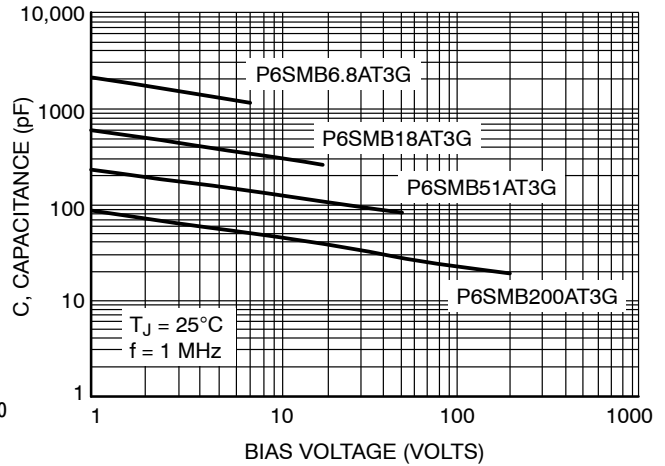
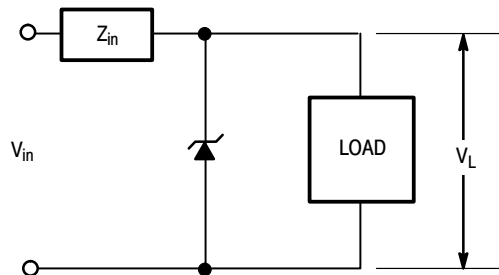


Figure 4. Typical Junction Capacitance vs. Bias Voltage

TYPICAL PROTECTION CIRCUIT



APPLICATION NOTES

RESPONSE TIME

In most applications, the transient suppressor device is placed in parallel with the equipment or component to be protected. In this situation, there is a time delay associated with the capacitance of the device and an overshoot condition associated with the inductance of the device and the inductance of the connection method. The capacitive effect is of minor importance in the parallel protection scheme because it only produces a time delay in the transition from the operating voltage to the clamp voltage as shown in Figure 5.

The inductive effects in the device are due to actual turn-on time (time required for the device to go from zero current to full current) and lead inductance. This inductive effect produces an overshoot in the voltage across the equipment or component being protected as shown in Figure 6. Minimizing this overshoot is very important in the application, since the main purpose for adding a transient suppressor is to clamp voltage spikes. The SMB series have a very good response time, typically < 1 ns and negligible inductance. However, external inductive effects could produce unacceptable overshoot. Proper circuit layout,

minimum lead lengths and placing the suppressor device as close as possible to the equipment or components to be protected will minimize this overshoot.

Some input impedance represented by Z_{in} is essential to prevent overstress of the protection device. This impedance should be as high as possible, without restricting the circuit operation.

DUTY CYCLE DERATING

The data of Figure 1 applies for non-repetitive conditions and at a lead temperature of 25°C. If the duty cycle increases, the peak power must be reduced as indicated by the curves of Figure 7. Average power must be derated as the lead or ambient temperature rises above 25°C. The average power derating curve normally given on data sheets may be normalized and used for this purpose.

At first glance the derating curves of Figure 7 appear to be in error as the 10 ms pulse has a higher derating factor than the 10 μ s pulse. However, when the derating factor for a given pulse of Figure 7 is multiplied by the peak power value of Figure 1 for the same pulse, the results follow the expected trend.

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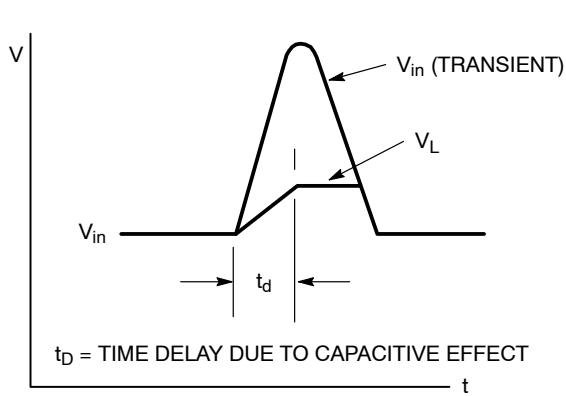


Figure 5.

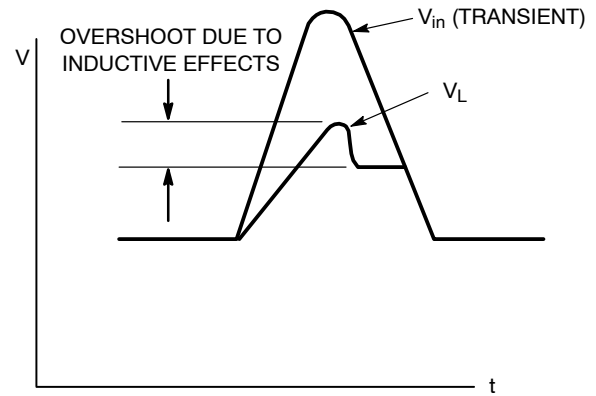


Figure 6.

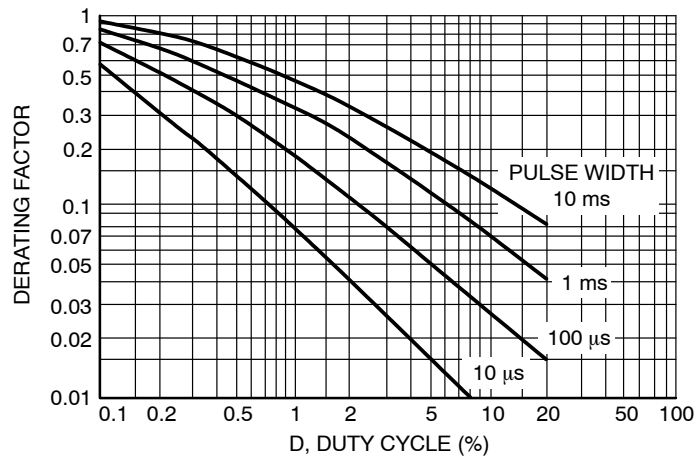


Figure 7. Typical Derating Factor for Duty Cycle

UL RECOGNITION

The entire series has *Underwriters Laboratory Recognition* for the classification of protectors (QVGQ2) under the UL standard for safety 497B and File #E210057. Many competitors only have one or two devices recognized or have recognition in a non-protective category. Some competitors have no recognition at all. With the UL497B recognition, our parts successfully passed several tests

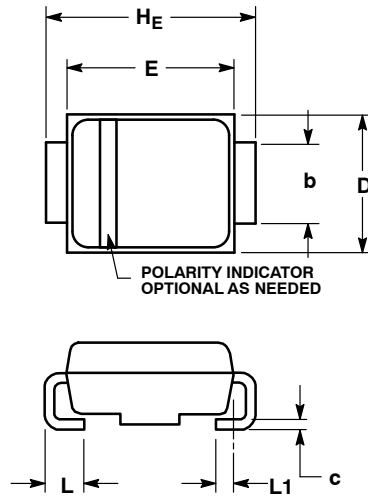
including Strike Voltage Breakdown test, Endurance Conditioning, Temperature test, Dielectric Voltage-Withstand test, Discharge test and several more.

Whereas, some competitors have only passed a flammability test for the package material, we have been recognized for much more to be included in their Protector category.

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PACKAGE DIMENSIONS

SMB CASE 403A-03 ISSUE H

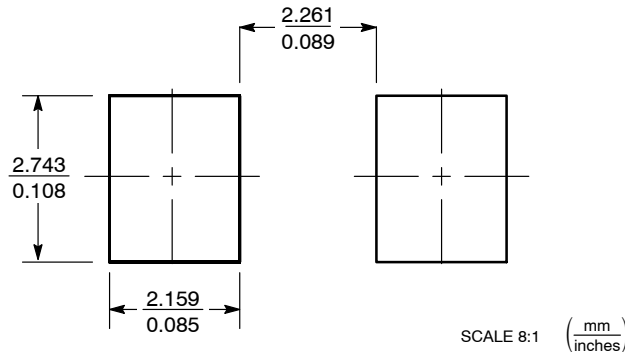


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.


DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.90	2.20	2.28	0.075	0.087	0.090
A1	0.05	0.10	0.19	0.002	0.004	0.007
b	1.96	2.03	2.20	0.077	0.080	0.087
c	0.15	0.23	0.31	0.006	0.009	0.012
D	3.30	3.56	3.95	0.130	0.140	0.156
E	4.06	4.32	4.60	0.160	0.170	0.181
H_E	5.21	5.44	5.60	0.205	0.214	0.220
L	0.76	1.02	1.60	0.030	0.040	0.063
L1	0.51 REF			0.020 REF		

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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